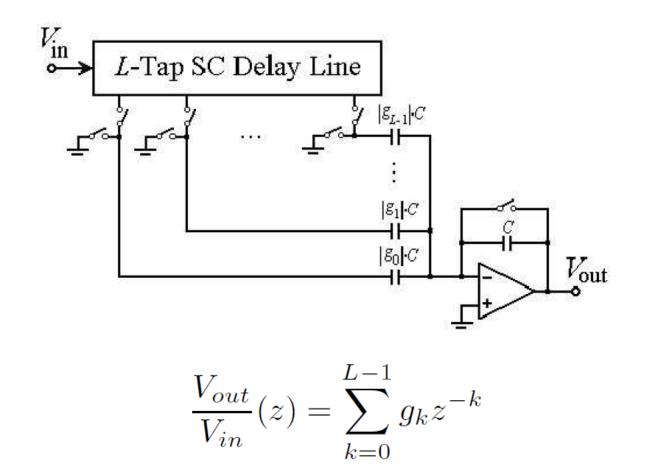
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# **Direct-Form SC Filters**

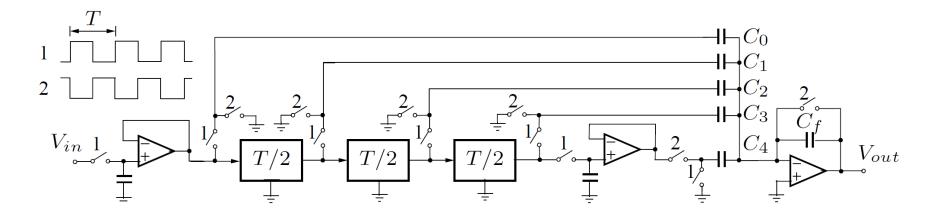
## **Direct-Form FIR SC Filter Realization**

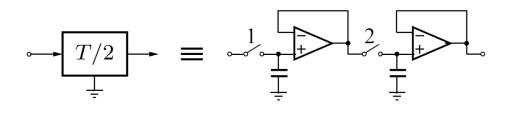
(L-1)th-order FIR SC filter:



# **Direct-Form FIR SC Filter Realization**

Ex.: 4<sup>th</sup>-order SC FIR filter

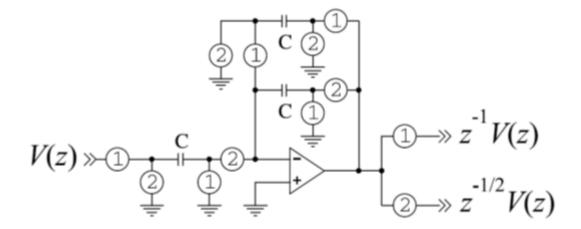




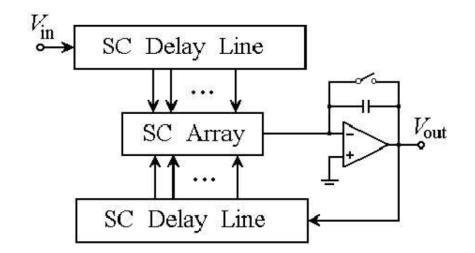
 $\frac{V_{out}}{V_{in}}(z) = -\frac{C_0}{C_f} - \frac{C_1}{C_f} z^{-1} - \frac{C_2}{C_f} z^{-2} - \frac{C_3}{C_f} z^{-3} + \frac{C_4}{C_f} z^{-4}$ 

## **Direct-Form FIR SC Filter Realization**

Reduction of the number of amplifiers by a multiplexing technique

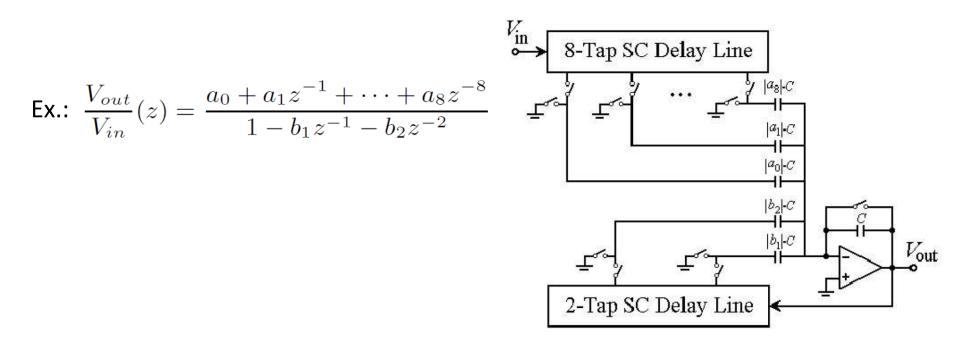


### **Direct-Form IIR SC Filter Realization**

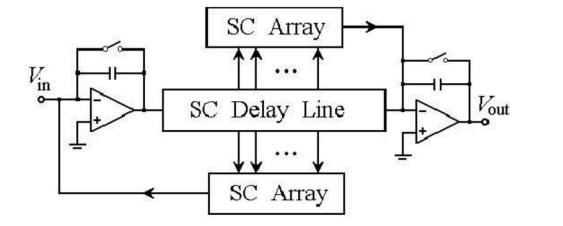


#### Direct Form I

2 SC delay lines sharing the same SC array

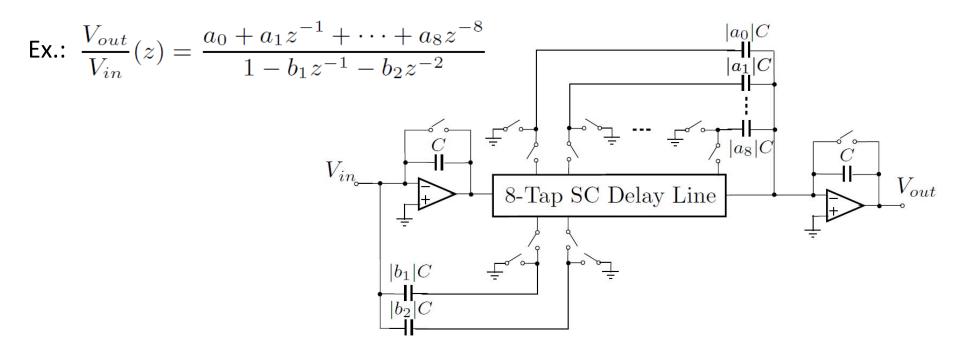


### **Direct-Form IIR SC Filter Realization**



#### Direct Form II

2 SC arrays sharing the same SC delay line



# **Capacitors in CMOS Technology**

### **Aplications in which capacitance matching is critical issue:**

- Converters: A/D, D/A, DC/DC
- Switched-capacitor filters

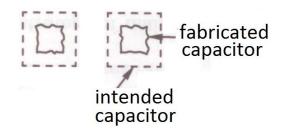
### **Capacitance mismatch sources in CMOS IC's:**

- Process gradient ( $t_{ox}$ )
- Random errors

# **Capacitors in CMOS Technology**

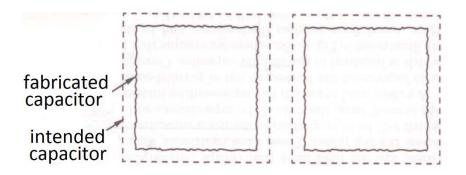
#### **Capacitors too small:**

- The actual capacitance ratio can be significantly different from unity.



#### Larger capacitors:

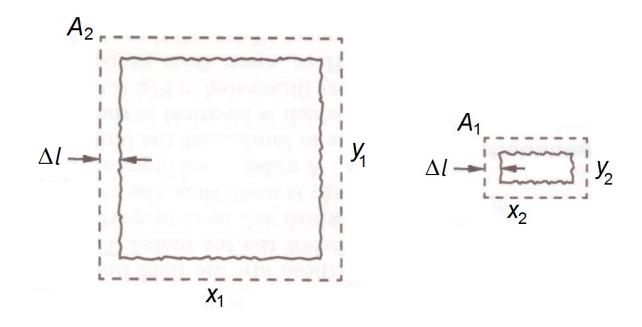
- Better ratio accuracy;
- However, if the plates are too large: (i) chip area may be excessive;
  (ii) opposite regions of the two capacitors may be affected differently by the fabrication process (e.g., slightly difference in oxide thickness);



# **Capacitors in CMOS Technology**

#### Sistematic errors:

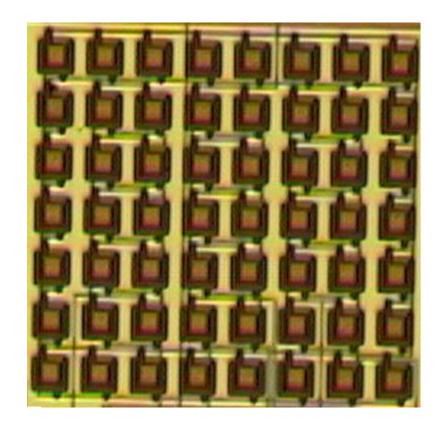
- The relative area error of two capacitors will be the same if the nominal perimeter/area ratio is the same;
- Therefore the capacitance ratio will not be affected.



# **Capacitor Layout**

**Techniques to improve capacitance matching:** 

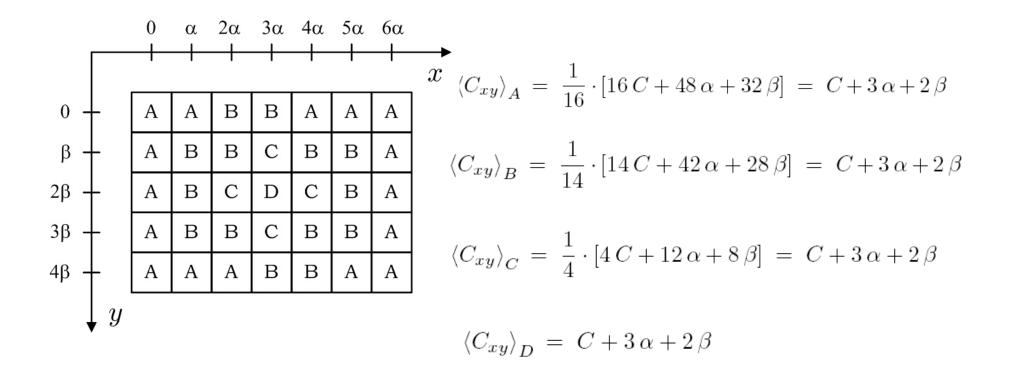
- Parallel connection of identical unit capacitors to implement each capacitance;
- Arrangement of unit capacitors in common centroid symmetry;
- Careful routing inside capacitor matrices.



Unit capacitor arrangement: C = 100 fF, 5μmx5μm

### **Capacitor Layout**

Common centroid geometry - evaluation of the mean unit capacitance of each capacitor, assuming the linear model for  $t_{ox}$ :





#### **Difficulties:**

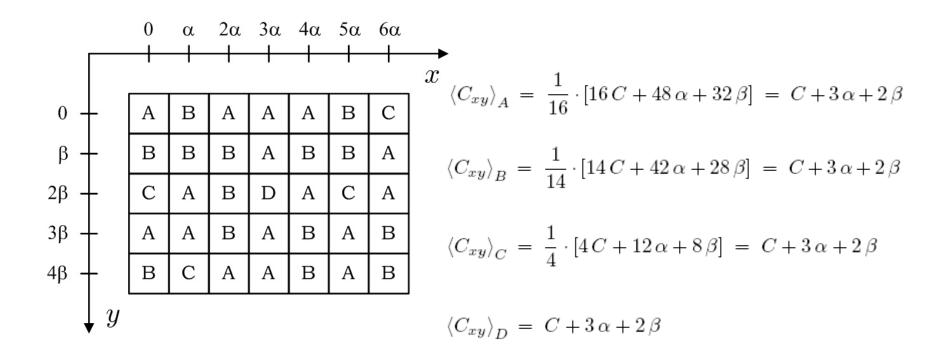
- Common centroid arrangement is not a simple task when the number of capacitance ratios is large;
- Common centroid geometry is not always possible;
- When it is possible, there are several alternatives;

#### **Solutions:**

- Develop an algorithm to search for the best arrangement among different possibilities;
- Find the optimal arrangement that doesn't have symmetry when common centroid is not possible.

### **Capacitor Layout**

Example without common centroid, but insensitive to process gradient:



C.F.T. Soares, A.C.M. Filho and A. Petraglia, IEEE Trans. Evolutionary Computation, Jun. 2010.

## **Capacitance Mismatch Effects**

Mathematical model commonly used in computer aided analysis of SC filters:

$$\hat{\gamma_k} = \gamma_k + \epsilon_{\gamma_k}$$

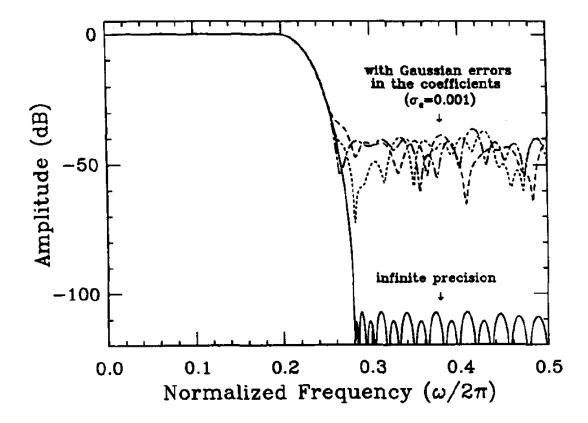
were  $\epsilon_{\gamma_k} = \gamma_k \epsilon_k$ 

 $\gamma_k$  : capacitance ratios

 $\epsilon_k$ : uncorrelated zero-mean Gaussian random variables

### **Capacitance Mismatch Effects**

Ex.: Frequency responses of 3 FIR filters having L = 50 and  $\sigma_e$  = 0.001



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